light at a *second wavelength*. In order to emit the *different wavelengths*, the different laser resonators have active layers (i.e., light emitting layers) of *different materials*. In certain embodiments, the active layers of the different resonators have *different* Group V elements (e.g., P, As, Sb, N) (page 7, lines 11-19; and page 8, lines 3-24). For example, in the Fig. 1 embodiment, the active layer 113 of one resonator is of AlGaAs, whereas the active layer 122 of the other resonator is of GaInP (i.e., note the different Group V elements As and P). Moreover, a high resistance region (e.g., 141) is provided between the resonators in order to electrically isolate the resonators (page 9, lines 7-14; page 10, lines 6-19; and page 16, lines 3-6). In the Fig. 1 embodiment, for example, the high resistance region 141 may be formed by implanting Ga ions and/or protons into the sidewall of the groove 160 (page 16, lines 3-6). In certain embodiments, a current path can be formed in the high resistance region via impurity diffusion 142 (page 10, lines 15-19; and page 16, lines 8-12).

Claim 1 stands rejected under 35 U.S.C. Section 102(e) as being allegedly anticipated by Tanaka. This Section 102(e) rejection is respectfully traversed for at least the following reasons.

Claim 1 requires "a plurality of semiconductor laser resonators having <u>different light emitting active layers of materials different from each other</u>, the semiconductor laser resonators being provided on the same semiconductor substrate so that the light emitting active layers lie substantially in parallel to a main surface of the semiconductor substrate, and a high-resistance region provided between the semiconductor laser resonators." In other words, claim 1 requires that the light emitting layers (i.e., active layers) of the

different resonators be of different materials. This enables the different resonators to emit different wavelengths in a desirable manner. For example, see Fig. 1 of the instant application which illustrates different light emitting active layers 113 and 122 of materials different from one another. The cited art fails to disclose or suggest this aspect of claim 1.

Tanaka *fails* to disclose or suggest different active layers of different materials. Instead, the semiconductor laser of Tanaka includes only one active layer (e.g., see active layer 4 in Fig. 1 of Tanaka). Since there is only one active layer in Tanaka, the reference cannot possibly meet the requirement of claim 1 of "a plurality of semiconductor laser resonators having different light emitting active layers of materials different from each other." Tanaka is entirely unrelated to the invention of claim 1 in this respect.

Claim 16 (not amended herein) requires "first and second semiconductor laser resonators provided on the same semiconductor substrate, an active layer of the first laser resonator being of a different material than an active layer of the second laser resonator." Again, Tanaka clearly fails to disclose or suggest the first and second different active layers required by claim 16. Tanaka has only one active layer, and cannot possibly meet the aforesaid underlined aspect of claim 16.

As for the §103(a) rejection of claim 11, it appears as if the Examiner has made a typographical error (Motoda is referenced instead of Tanaka). The Motoda reference was distinguished in a previous Amendment. In particular, Motoda fails to disclose or suggest the plurality of semiconductor laser resonators having light emitting layers of

different materials as recited in claim 1. Citation to Doi cannot overcome the fundamental flaws of Motoda in this regard.

For at least the foregoing reasons, it is respectfully requested that all rejections be withdrawn. All claims are in condition for allowance. If any minor matter remains to be resolved, the Examiner is invited to telephone the undersigned with regard to the same.

Respectfully submitted,

NIXON & VANDERHYE P.C.

By: _____
Joseph A. Rhoa
Reg. No. 37,515

JAR:caj
1100 North Glebe Road, 8th Floor
Arlington, VA 22201-4714
Telephone: (703) 816-4000
Facsimile: (703) 816-4100

VERSION WITH MARKINGS TO SHOW CHANGES MADE IN THE CLAIMS

1. (*Amended*) A semiconductor laser device comprising:

a plurality of semiconductor laser resonators having different light emitting active layers of materials different from each other, the semiconductor laser resonators being provided on the same semiconductor substrate so that the light emitting active layers lie substantially in parallel to a main surface of the semiconductor substrate, and

a high-resistance region provided between the semiconductor laser resonators.

16. (*Unamended*) A semiconductor laser device comprising:

first and second semiconductor laser resonators provided on the same semiconductor substrate, an active layer of the first laser resonator being of a different material than an active layer of the second laser resonator;

the active layer of the second laser resonator being provided in a groove, whereas the active layer of the first laser resonator is not provided in a groove; and

a high-resistance region provided at least along a sidewall of the groove in which the active layer of the second laser resonator is provided, the high-resistance region comprising ions and/or protons implanted into the sidewall of the groove.